

U.S. Department of Commerce, Patent and Trademark Office				Atty. Docket No.		Serial No.		
				M-15212 US		Unassigned		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s)				
(Use several sheets if necessary)				Chia-Shun Hsiao et al.				
				Filing Date		Group		
				Herewith		Unassigned		
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
WD	AA	2003/0067806	10 Apr. 2003	Tuan				
WD	AB	6,355,524	12 Mar. 2002	Tuan et al.				
WD	AC	6,541,324	1 Apr. 2003	Wang				
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
WD	AQ	K. Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on Its Source Side", IEDM Technical Digest 1989, pages 603-606.						
WD	AR	United States Application No.: 10/402,698 filed March 28, 2003 by Chung et al.						
WD	AS	R. Mih et al., "0.18um Modular Triple Self-Aligned Embedded Split-Gate Flash Memory", 2000 Symposium on VLSI Technology, Digest of Technical Papers, pages 120-121.						
Examiner		Date Considered						
J. M. Sullivan		04/26/2005						
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								